7MBR30XKA065-50

IGBT Modules

Power Module(X series)
650V / 30A / PIM

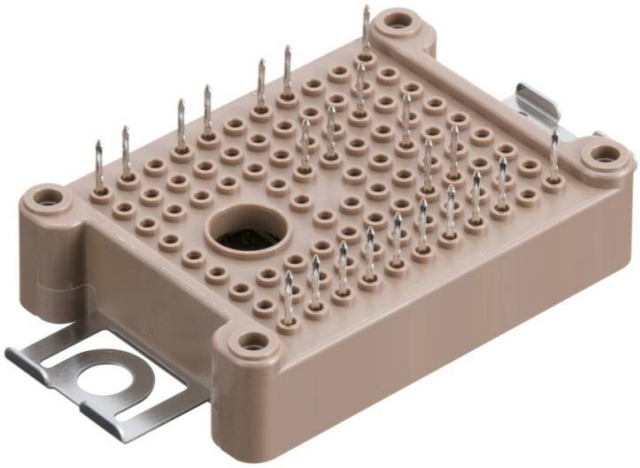
■ Features

Low $V_{CE(sat)}$
Compact Package
P.C.Board Mount Module
Converter Diode Bridge Dynamic Brake Circuit
RoHS compliant Product

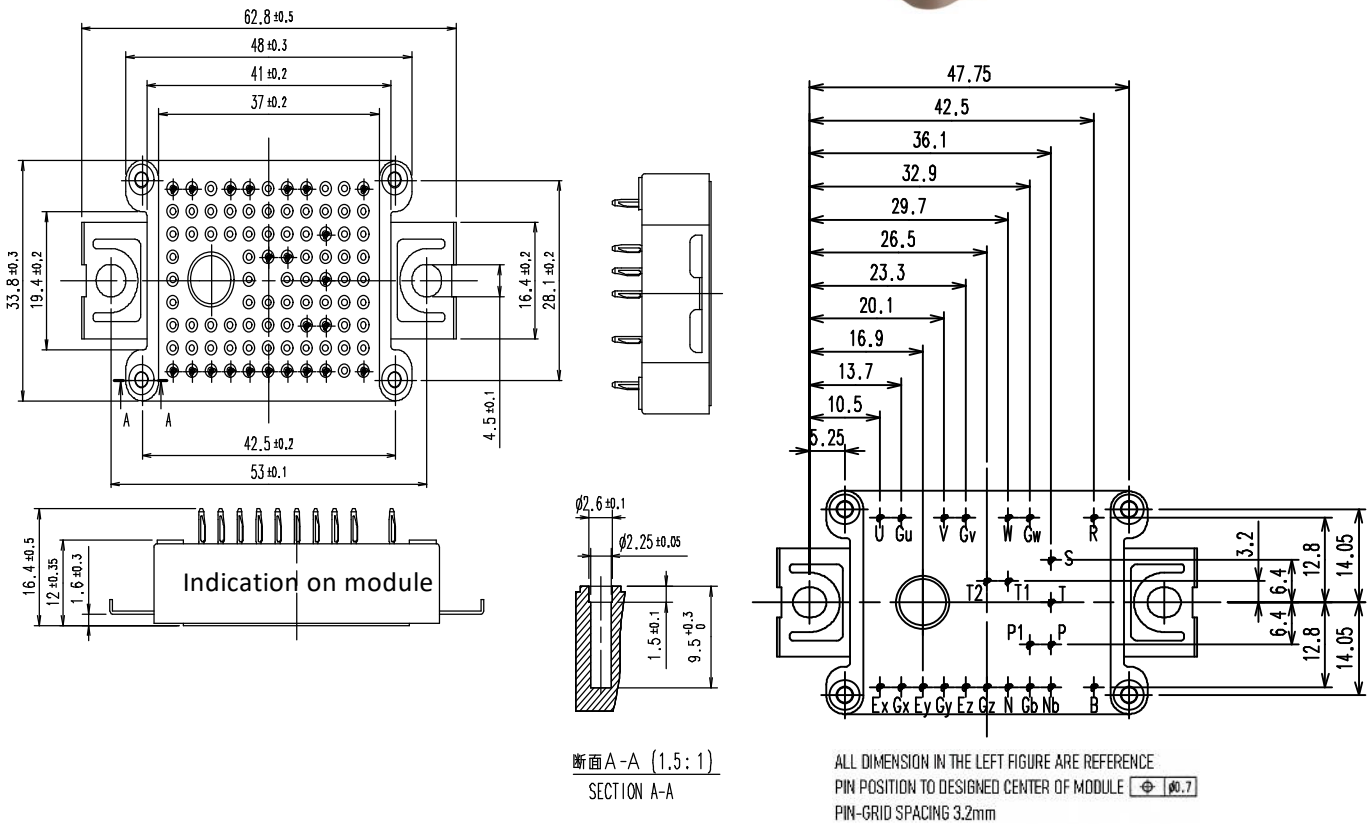
■ Applications

Inverter for Motor Drive
AC and DC Servo Drive Amplifier
Uniterruptible Power Supply

■ Typical appearance



■ Outline drawing (Unit : mm)



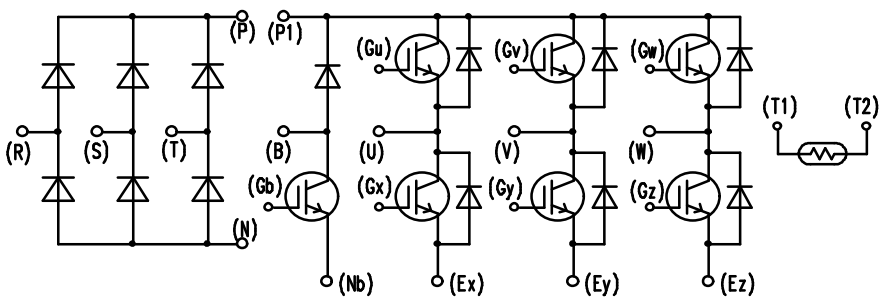
断面A-A (1.5:1)
SECTION A-A

ALL DIMENSION IN THE LEFT FIGURE ARE REFERENCE
PIN POSITION TO DESIGNED CENTER OF MODULE ⌖ ϕ0.7
PIN-GRID SPACING 3.2mm

Weight: 25 g (typ.)

■ Equivalent circuit

[Converter] [Brake] [Inverter] [Thermistor]



■ Maximum ratings (at T_c = 25°C unless otherwise specified)

	Items	Symbols	Conditions		Maximum ratings	Units
Inverter	Collector-Emitter voltage, Gate-Emitter short-circuited	V_{CES}			650	V
	Gate-Emitter voltage, Cllector-Emitter short-circuited	V_{GES}			±20	V
	Collector current	I_C	Continuous	T_c=100°C	30	A
	Repetitive peak collector current	I_{CRM}	1ms		60	
	Forward current	I_F	Continuous		30	
	Repetitive peak forward current	I_{FRM}	1ms		60	
	Total power dissipation	P_{tot}	1 device		180	W
Brake IGBT	Collector-Emitter voltage, Gate-Emitter short-circuited	V_{CES}			650	V
	Gate-Emitter voltage, Collector-Emitter short-circuited	V_{GES}			±20	V
	Collector current	I_C	Continuous	T_c=100°C	30	A
	Repetitive peak collector current	I_{CRM}	1ms		60	
	Total power dissipation	P_{tot}	1 device		180	W
Brake FWD	Forward current	I_F	Continuous		10	A
	Repetitive peak forward current	I_{FRM}	1ms		20	
	Repetitive peak reverse voltage	V_{RRM}			650	V
Converter	Repetitive peak reverse voltage	V_{RRM}			800	V
	Average output current	I_O	Three-phase full wave rectified current	T_c=80°C	30	A
	Surge forward current (Non-Repetitive) (*1)	I_{FSM}	t=10ms, Half sine wave form	T_{vj}=25°C	390	A
				T_{vj}=150°C	340	
	I^2t (Non-Repetitive) (*1)	I^2t		T_{vj}=25°C	760	A^2s
				T_{vj}=150°C	585	
Virtual junction temperature		T_{vj}	Inverter, Brake		175	°C
			Converter		150	
Operating virtual junction temperature (under switching conditions)		T_{vjop}	Inverter, Brake		175	
			Converter		150	
Case temperature		T_c			125	
Storage temperature		T_{stg}			-40 ~ 125	
Isolation voltage	Between terminals and copper base (*2) Between thermistor and others (*3)	V_{isol}	A.C. : 1min.		2500	Vrms
Screw torque	Mounting torque of screws to heat sink	M_s	M4		1.3～1.7	N·m

(*1) T_{vj} : Temperature at test start.

(*2) All terminals should be connected together during the test.

(*3) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

■ **Electrical characteristics (at T_{vj} = 25°C unless otherwise specified)**

	Items	Symbols	Conditions		Characteristics min.	Characteristics typ.	Characteristics max.	Units
Inverter	Collector-Emitter cut-off current, Gate-Emitter short-circuited	I_{CES}	V_{GE} = 0V V_{CE} = 650V		-	-	50	μA
	Gate leakage current, Collector-Emitter short-circuited	I_{GES}	V_{CE} = 0V V_{GE} = +20/-20V		-	-	100	nA
	Gate-Emitter threshold voltage	$V_{GE(th)}$	V_{CE} = 20V I_C = 30mA		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	V_{GE} = 15V I_C = 30A	T_{vj}=25°C	-	1.55	2.05	V
		$V_{CE(sat)}$ (chip)		T_{vj}=25°C	-	1.30	1.75	
				T_{vj}=125°C	-	1.45	-	
				T_{vj}=150°C	-	1.50	-	
				T_{vj}=175°C	-	1.55	-	
	Internal gate resistance	r_g	-		-	0	-	Ω
	Capacitance	C_{ies}	V_{CE} = 10V, V_{GE} =0V, f = 1MHz		-	3.4	-	nF
		C_{oes}			-	0.13	-	
		C_{res}			-	0.05	-	
	Gate charge	Q_G	V_{CC} = 300V V_{GE}=-15 → +15V I_C = 30A		-	240	-	nC
	Forward voltage	V_F (terminal)	I_F = 30A	T_{vj}=25°C	-	2.10	2.60	V
		V_F (chip)		T_{vj}=25°C	-	1.85	2.30	
				T_{vj}=125°C	-	1.90	-	
				T_{vj}=150°C	-	1.85	-	
				T_{vj}=175°C	-	1.85	-	
	Switching time (*1)	$t_{d(on)}$	V_{CC} = 300V I_C,I_F = 30A L_s = 30nH V_{GE} = +15/-15 V R_G = 15 Ω	T_{vj}=25°C	-	0.06	-	μs
				T_{vj}=125°C	-	0.06	-	
				T_{vj}=150°C	-	0.06	-	
				T_{vj}=175°C	-	0.06	-	
		t_r	V_{CC} = 300V I_C,I_F = 30A L_s = 30nH V_{GE} = +15/-15 V R_G = 15 Ω	T_{vj}=25°C	-	0.02	-	
				T_{vj}=125°C	-	0.03	-	
				T_{vj}=150°C	-	0.03	-	
				T_{vj}=175°C	-	0.03	-	
		$t_{d(off)}$	V_{CC} = 300V I_C,I_F = 30A L_s = 30nH V_{GE} = +15/-15 V R_G = 15 Ω	T_{vj}=25°C	-	0.16	-	
				T_{vj}=125°C	-	0.18	-	
				T_{vj}=150°C	-	0.19	-	
				T_{vj}=175°C	-	0.19	-	
		t_f	V_{CC} = 300V I_C,I_F = 30A L_s = 30nH V_{GE} = +15/-15 V R_G = 15 Ω	T_{vj}=25°C	-	0.04	-	
				T_{vj}=125°C	-	0.04	-	
				T_{vj}=150°C	-	0.04	-	
				T_{vj}=175°C	-	0.04	-	
	Reverse recovery time	t_{rr}	V_{CC} = 300V I_C,I_F = 30A L_s = 30nH V_{GE} = +15/-15 V R_G = 15 Ω	T_{vj}=25°C	-	0.07	-	
				T_{vj}=125°C	-	0.11	-	
				T_{vj}=150°C	-	0.12	-	
				T_{vj}=175°C	-	0.14	-	

(*1) Turn on time (t_{on}) = $t_{d(on)}$ + t_r , Turn off time (t_{off}) = $t_{d(off)}$ + t_f

	Items	Symbols	Conditions		Characteristics min.	typ.	max.	Units
Inverter	Switching loss (per pulse)	E_{on}	V_{CC} = 300V, I_C,I_F = 30A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 15 Ω	T_{vj}=25°C	-	0.44	-	mJ
				T_{vj}=125°C	-	0.63	-	
				T_{vj}=150°C	-	0.71	-	
				T_{vj}=175°C	-	0.78	-	
		E_{off}	V_{CC} = 300V, I_C,I_F = 30A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 15 Ω	T_{vj}=25°C	-	0.82	-	
				T_{vj}=125°C	-	1.04	-	
				T_{vj}=150°C	-	1.12	-	
				T_{vj}=175°C	-	1.15	-	
		E_{rr}	V_{CC} = 300V, I_C,I_F = 30A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 15 Ω	T_{vj}=25°C	-	0.24	-	
				T_{vj}=125°C	-	0.38	-	
				T_{vj}=150°C	-	0.42	-	
				T_{vj}=175°C	-	0.50	-	
Brake	Collector-Emitter cut-off current, Gate-Emitter short-circuited	I_{CES}	V_{GE} = 0V, V_{CE} = 650V		-	-	50	μA
	Gate leakage current, Collector-Emitter short-circuited	I_{GES}	V_{CE} = 0V, V_{GE} = +20/-20V		-	-	100	nA
	Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	V_{GE} = 15V, I_C = 30A	T_{vj}=25°C	-	1.55	2.05	V
		$V_{CE(sat)}$ (chip)		T_{vj}=25°C	-	1.30	1.75	
				T_{vj}=125°C	-	1.45	-	
				T_{vj}=150°C	-	1.50	-	
				T_{vj}=175°C	-	1.55	-	
	Internal gate resistance	r_g	-		-	0	-	Ω
	Switching time (*1)	$t_{d(on)}$	V_{CC} = 300V, I_C = 30A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 15 Ω	T_{vj}=25°C	-	0.06	-	μs
				T_{vj}=125°C	-	0.06	-	
				T_{vj}=150°C	-	0.06	-	
				T_{vj}=175°C	-	0.06	-	
		t_r	V_{CC} = 300V, I_C = 30A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 15 Ω	T_{vj}=25°C	-	0.02	-	
				T_{vj}=125°C	-	0.03	-	
				T_{vj}=150°C	-	0.03	-	
				T_{vj}=175°C	-	0.03	-	
		$t_{d(off)}$	V_{CC} = 300V, I_C = 30A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 15 Ω	T_{vj}=25°C	-	0.16	-	
				T_{vj}=125°C	-	0.18	-	
				T_{vj}=150°C	-	0.19	-	
				T_{vj}=175°C	-	0.19	-	
		t_f	V_{CC} = 300V, I_C = 30A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 15 Ω	T_{vj}=25°C	-	0.04	-	
				T_{vj}=125°C	-	0.04	-	
				T_{vj}=150°C	-	0.04	-	
				T_{vj}=175°C	-	0.04	-	
	Reverse current	I_{RRM}	V_R = 650V		-	-	50	μA
	Forward voltage	V_F (terminal)	I_F = 10A	T_j=25°C	-	1.80	2.30	V
		V_F (chip)	I_F = 10A	T_{vj}=25°C	-	1.55	2.00	
				T_{vj}=125°C	-	1.50	-	
				T_{vj}=150°C	-	1.50	-	
				T_{vj}=175°C	-	1.45	-	
Converter	Reverse current	I_{RRM}	V_R = 800V		-	-	50	μA
	Continuous (direct) forward voltage	V_F	I_F = 30A	terminal	-	1.30	1.80	V
				chip	-	1.05	1.50	
Thermistor	Resistance	R	T = 25°C		-	5000	-	Ω
			T = 100°C		465	495	520	
	B value	B	T = 25/ 50°C		3305	3375	3450	K

(*1) Turn on time (t_{on}) = $t_{d(on)}$ + t_r , Turn off time (t_{off}) = $t_{d(off)}$ + t_f

NOTICE:
The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

■Thermal resistance characteristics

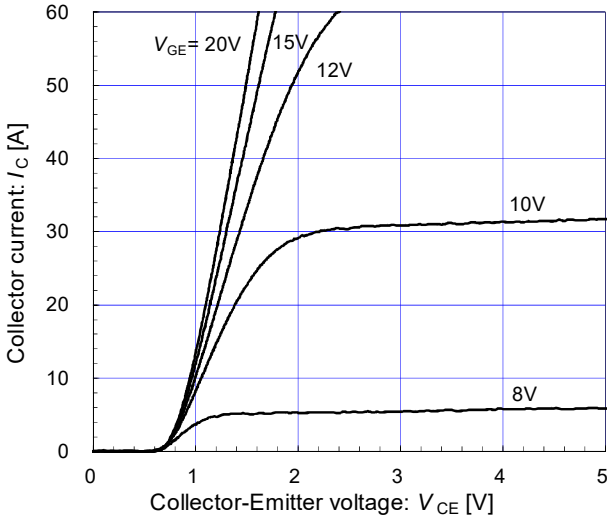
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance junction to case (1 device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.82	K/W
		Inverter FWD	-	-	1.50	
		Brake IGBT	-	-	0.82	
		Brake FWD	-	-	1.92	
		Converter Diode	-	-	0.75	
Thermal resistance case to heat sink(*1) (1 device)	$R_{th(c-s)}$	Inverter IGBT	-	0.75	-	
		Inverter FWD	-	0.92	-	
		Brake IGBT	-	0.78	-	
		Brake FWD	-	0.80	-	
		Converter Diode	-	0.79	-	

(*1) This is the value which is defined mounting on the additional cooling fin with 1 W/(m・K) thermal grease.

[Inverter]

Collector current vs. Collector-Emitter voltage (typ.)

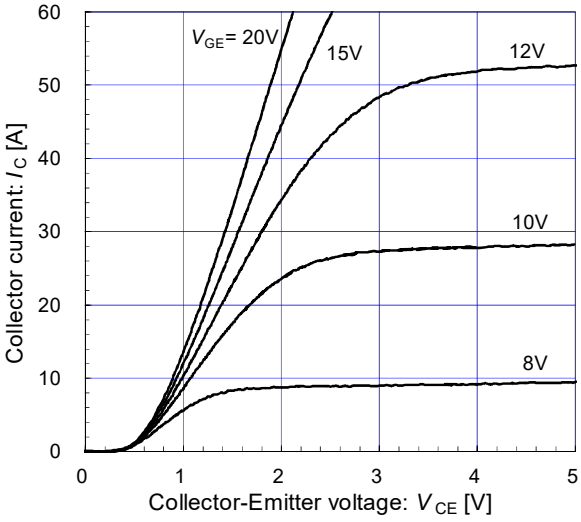
T_{vj}= 25°C / chip



[Inverter]

Collector current vs. Collector-Emitter voltage (typ.)

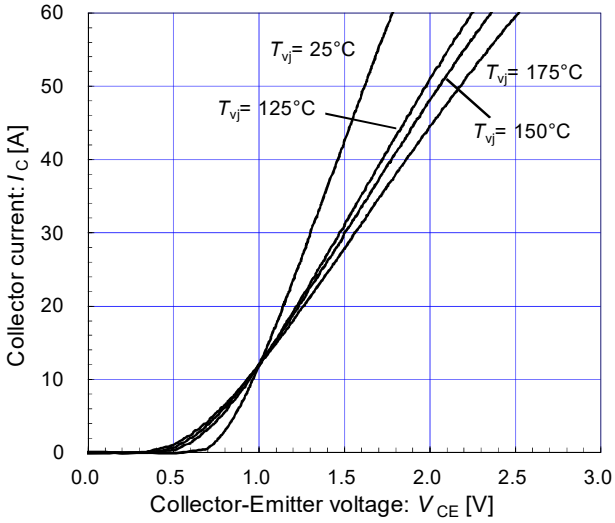
T_{vj}= 175°C / chip



[Inverter]

Collector current vs. Collector-Emitter voltage (typ.)

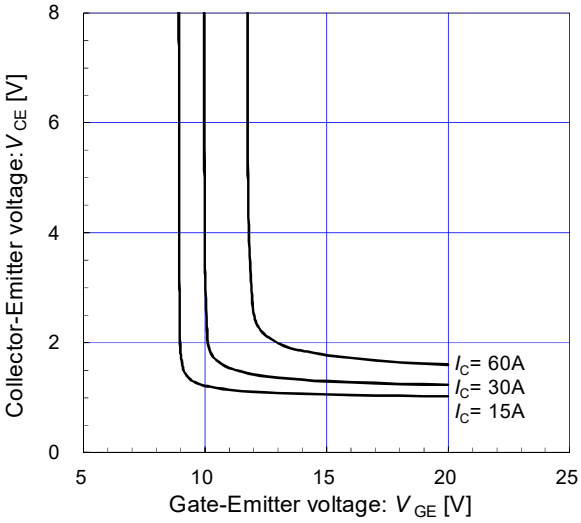
V_{GE}=15V / chip



[Inverter]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

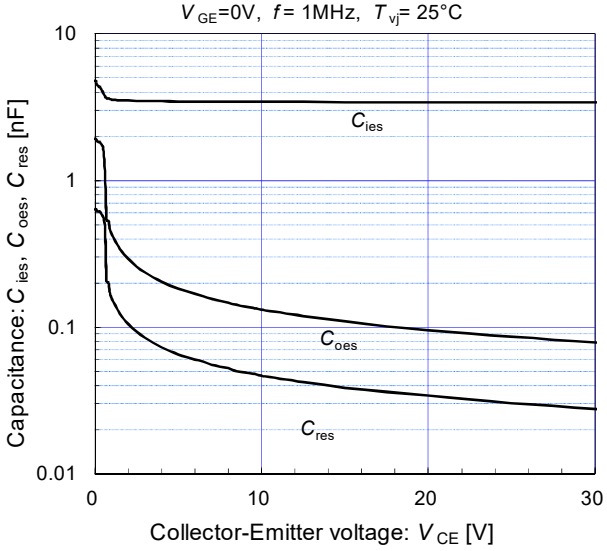
T_{vj}= 25°C / chip



[Inverter]

Capacitance vs. Collector-Emitter voltage (typ.)

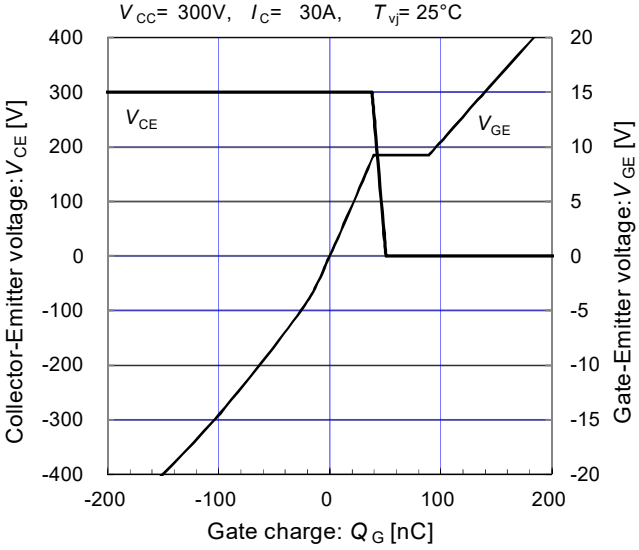
V_{GE}=0V, f= 1MHz, T_{vj}= 25°C



[Inverter]

Dynamic gate charge (typ.)

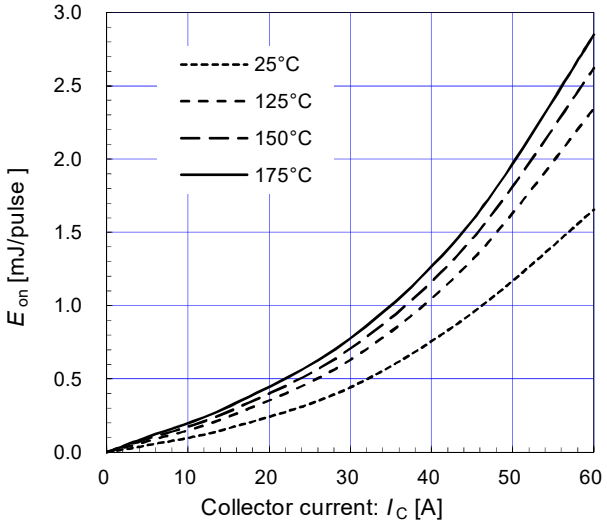
V_{CC}= 300V, I_C= 30A, T_{vj}= 25°C



[Inverter]

E_{on} vs. Collector current (typ.)

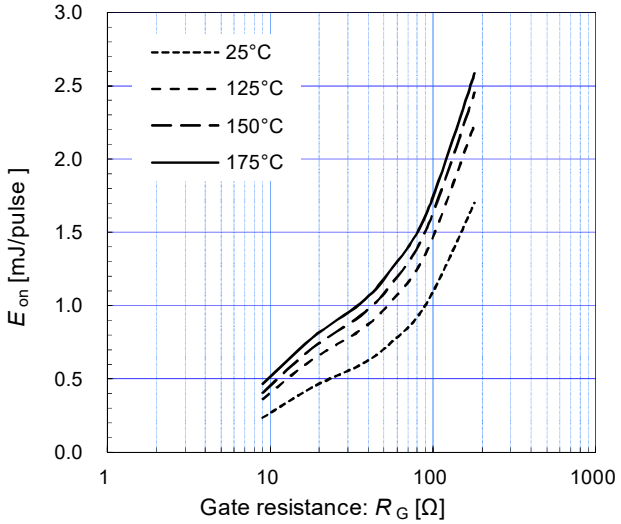
V_{CC}= 300V, V_{GE} = +15/-15 V, R_G= 15 Ω



[Inverter]

E_{on} vs. Gate resistance (typ.)

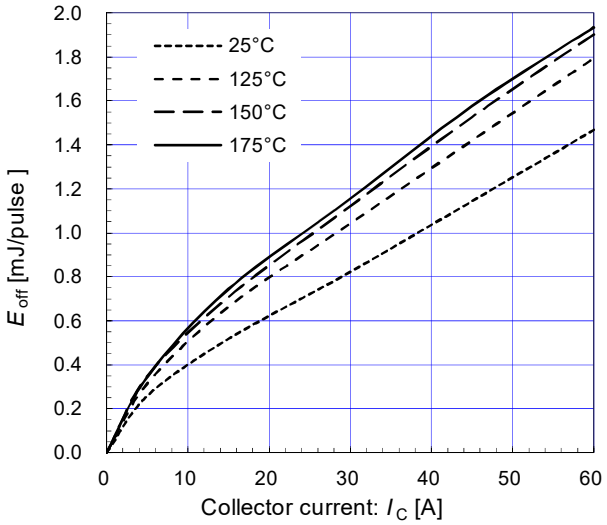
V_{CC}= 300V, V_{GE} = +15/-15 V, I_C= 30A



[Inverter]

E_{off} vs. Collector current (typ.)

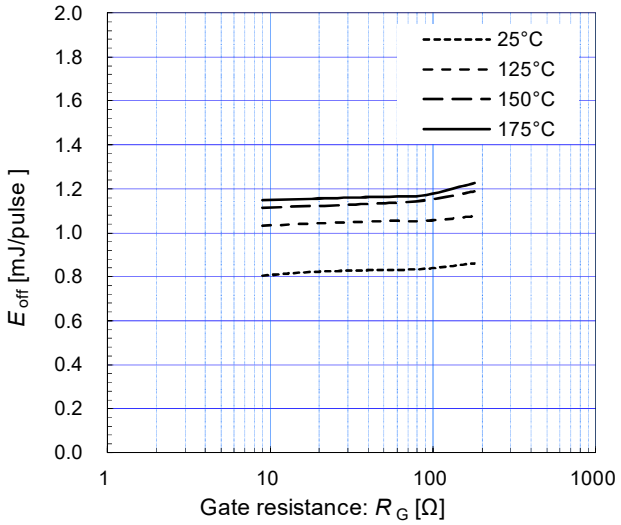
V_{CC}= 300V, V_{GE} = +15/-15 V, R_G= 15 Ω



[Inverter]

E_{off} vs. Gate resistance (typ.)

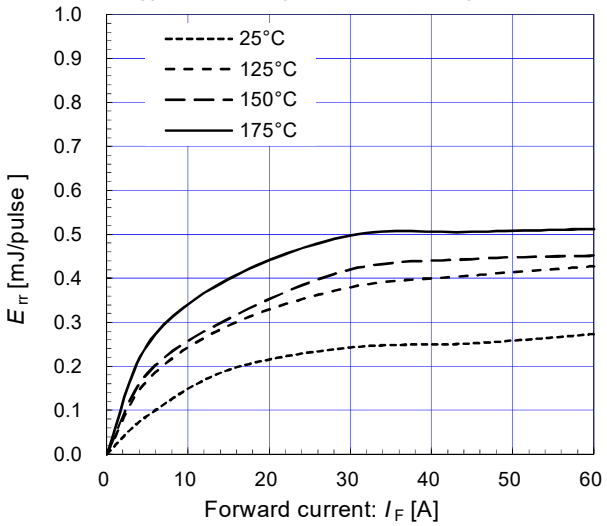
V_{CC}= 300V, V_{GE} = +15/-15 V, I_C= 30A



[Inverter]

E_{rr} vs. Forward current (typ.)

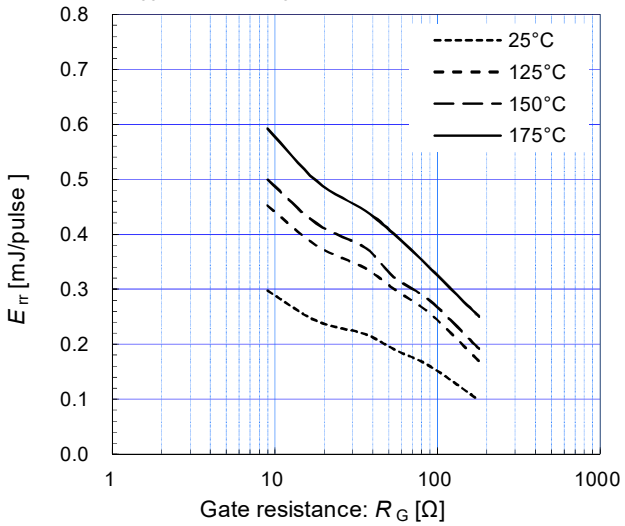
V_{CC}= 300V, V_{GE} = +15/-15 V, R_G= 15 Ω



[Inverter]

E_{rr} vs. Gate resistance (typ.)

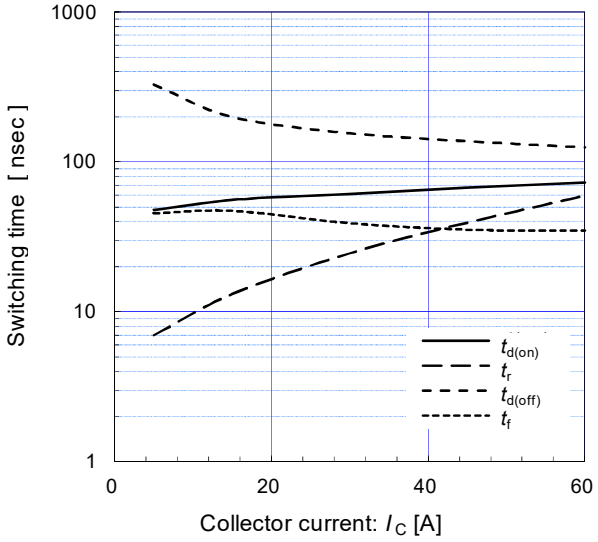
V_{CC}= 300V, V_{GE} = +15/-15 V, I_F= 30A



[Inverter]

Switching time vs. Collector current (typ.)

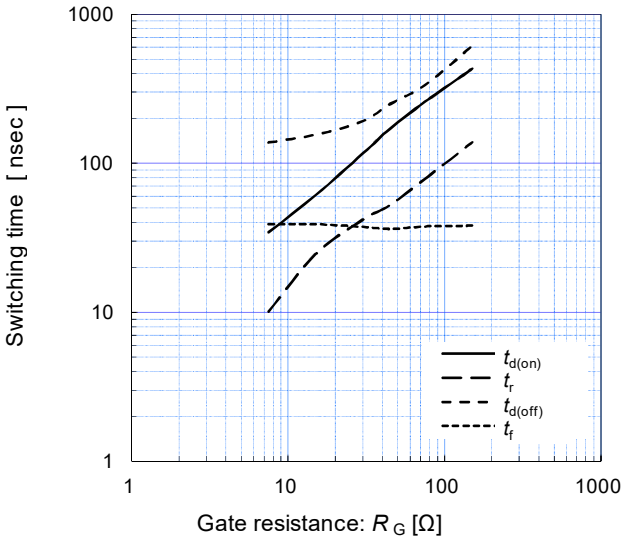
V_{CC}= 300V, R_G= 15Ω V_{GE}= +15/-15 V, T_{vj}= 25°C



[Inverter]

Switching time vs. Gate resistance (typ.)

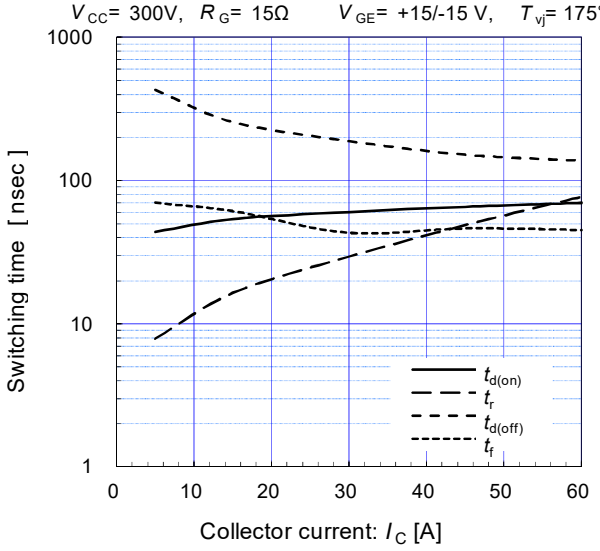
V_{CC}= 300V, I_C= 30A, V_{GE}= +15/-15 V, T_{vj}= 25°C



[Inverter]

Switching time vs. Collector current (typ.)

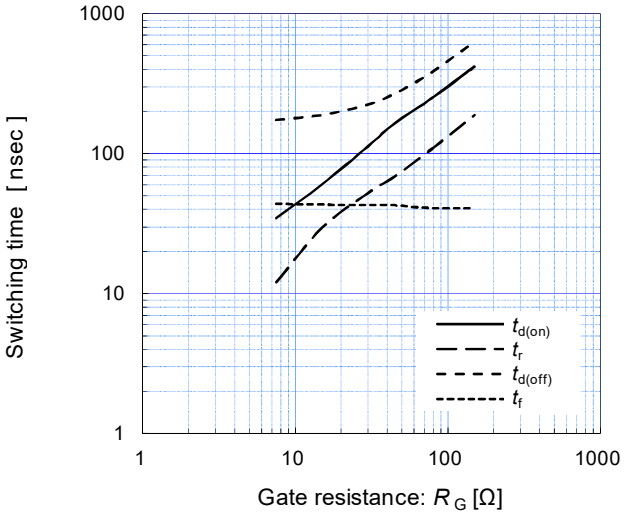
V_{CC}= 300V, R_G= 15Ω V_{GE}= +15/-15 V, T_{vj}= 175°C



[Inverter]

Switching time vs. Gate resistance (typ.)

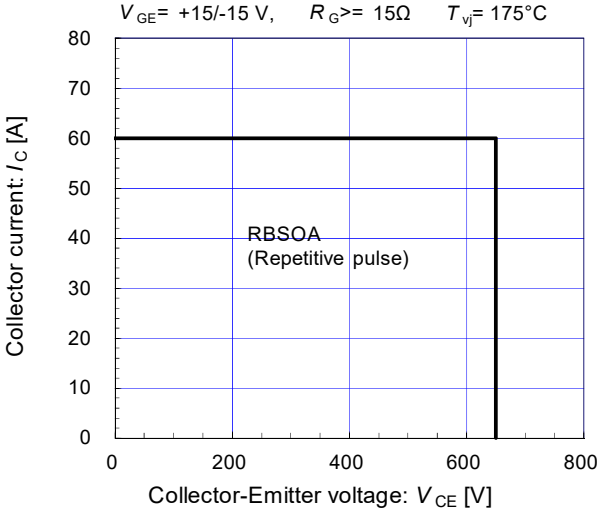
V_{CC}= 300V, I_C= 30A, V_{GE}= +15/-15 V, T_{vj}= 175°C



[Inverter]

Reverse bias safe operating area (max.)

V_{GE}= +15/-15 V, R_G>= 15Ω T_{vj}= 175°C

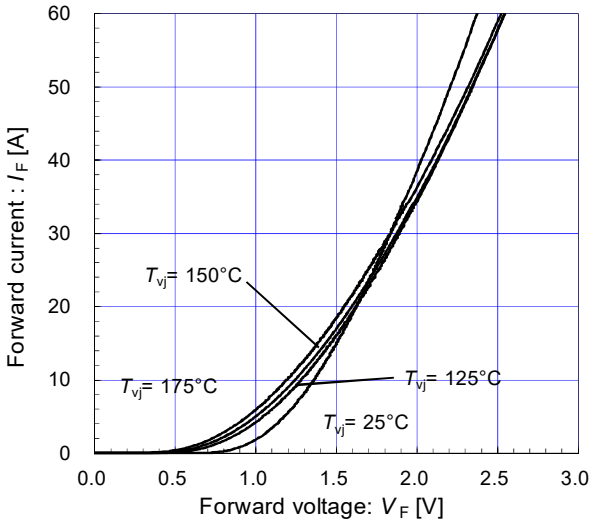


(Main terminals)

[Inverter]

Forward current vs. Forward voltage (typ.)

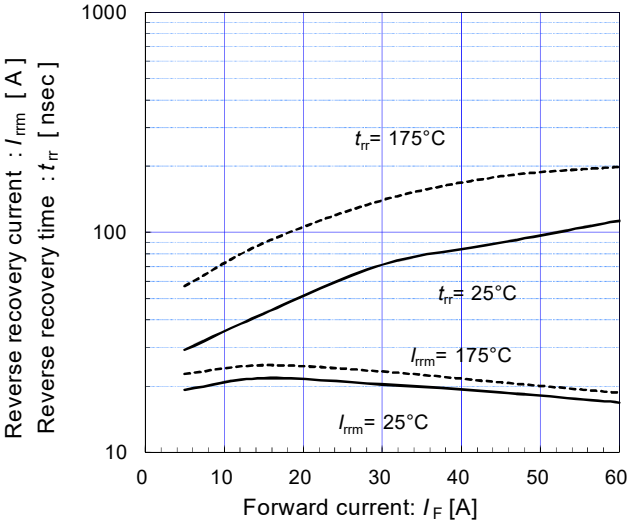
chip



[Inverter]

Reverse recovery characteristics (typ.)

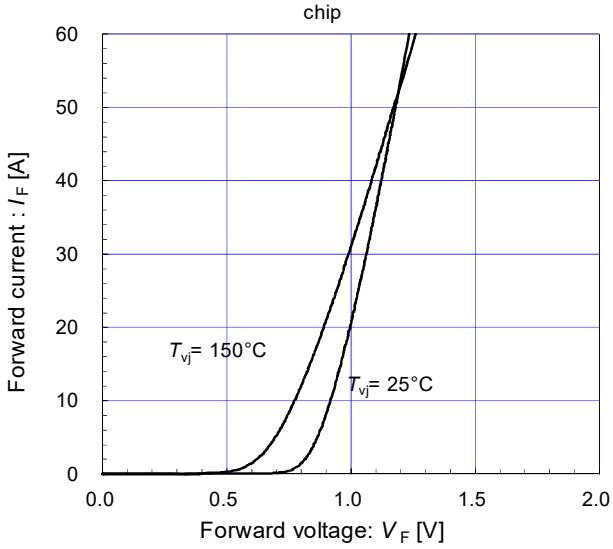
V_{CC}= 300V, V_{GE}= +15/-15 V, R_G= 15Ω



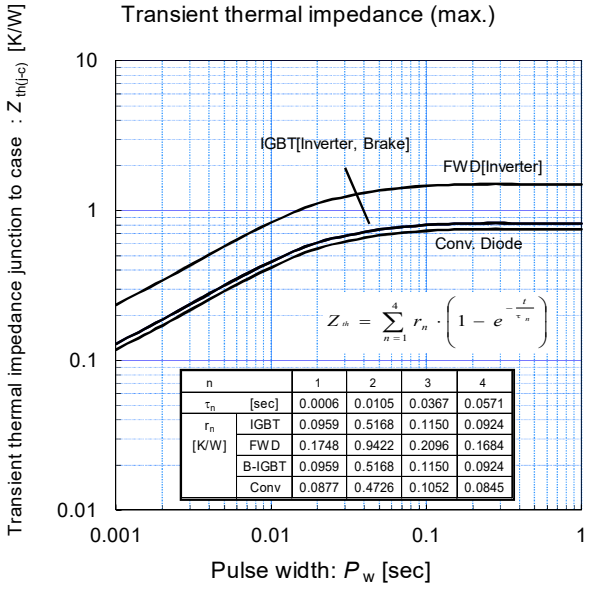
[Converter]

Forward current vs. Forward voltage (typ.)

chip



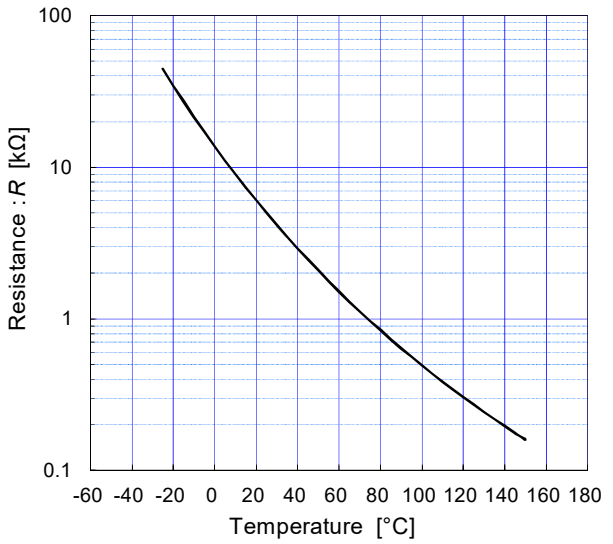
Transient thermal impedance (max.)



n		1	2	3	4
τ_n	[sec]	0.0006	0.0105	0.0367	0.0571
r_n [K/W]	IGBT	0.0959	0.5168	0.1150	0.0924
	FWD	0.1748	0.9422	0.2096	0.1684
	B-IGBT	0.0959	0.5168	0.1150	0.0924
	Conv	0.0877	0.4726	0.1052	0.0845

[Thermistor]

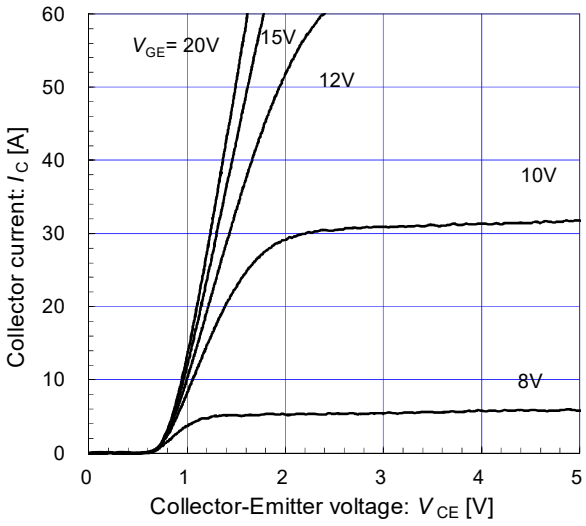
Temperature characteristic (typ.)



[Brake]

Collector current vs. Collector-Emitter voltage (typ.)

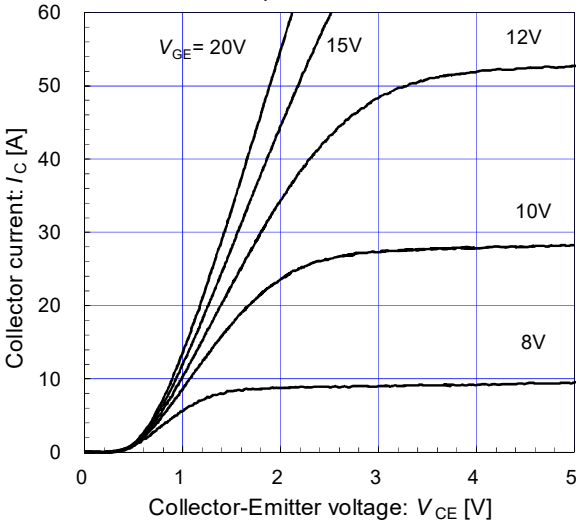
T_{vj}= 25°C / chip



[Brake]

Collector current vs. Collector-Emitter voltage (typ.)

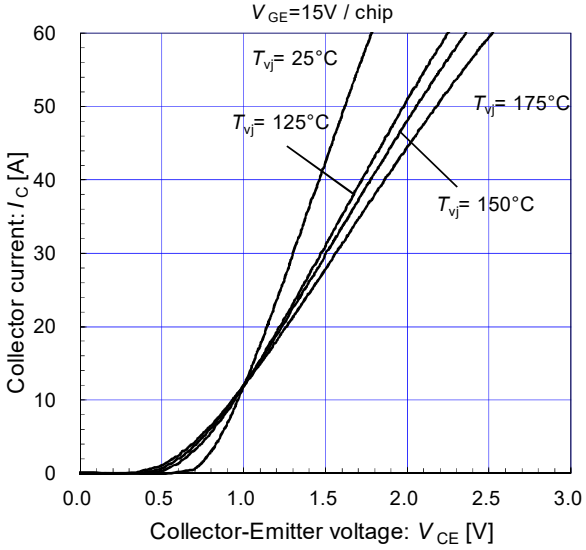
T_{vj}= 175°C / chip



[Brake]

Collector current vs. Collector-Emitter voltage (typ.)

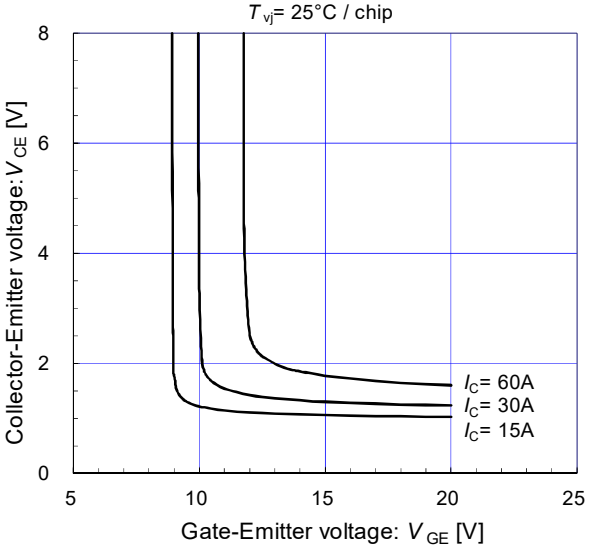
V_{GE}=15V / chip



[Brake]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

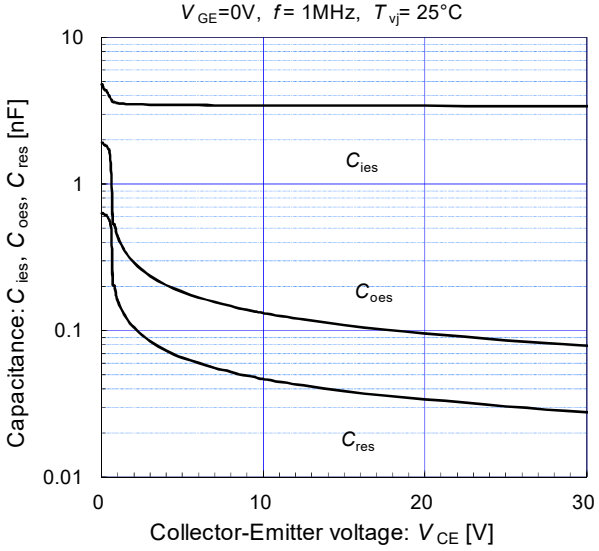
T_{vj}= 25°C / chip



[Brake]

Capacitance vs. Collector-Emitter voltage (typ.)

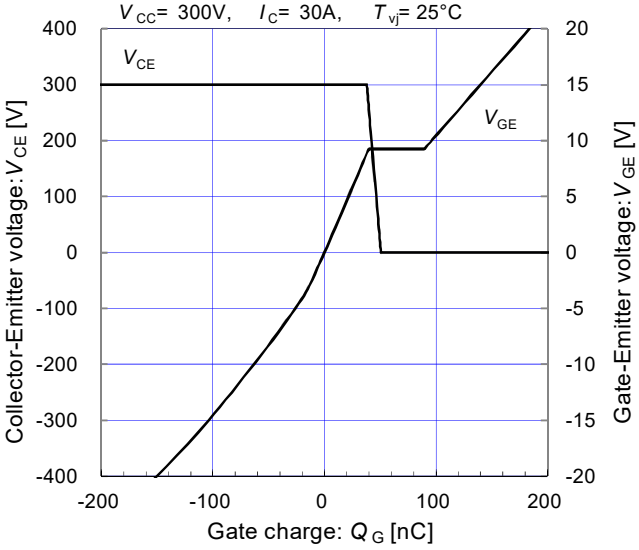
V_{GE}=0V, f= 1MHz, T_{vj}= 25°C



[Brake]

Dynamic gate charge (typ.)

V_{CC}= 300V, I_C= 30A, T_{vj}= 25°C



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1. This Catalog contains the product specifications, characteristics, data, materials, and structures as of 3/2023. The contents are subject to change without notice for specification changes or other reasons. When using a product listed in this Catalog, be sure to obtain the latest specifications.

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・Machine tools ・Audiovisual equipment ・Electrical home appliances ・Personal equipment ・Industrial robots etc.

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・Traffic-signal control equipment ・Gas leakage detectors with an auto-shut-off feature
・Emergency equipment for responding to disasters and anti-burglary devices ・Safety devices ・Medical equipment

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7.

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